

## **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the application:

### **Listing of Claims**

**Claim 1 (Currently amended):** MSM type photo-detection device designed to detect incident light and comprising reflecting means superposed on a first face of a support to form a first mirror for a Fabry-Pérot type resonant cavity, a layer of material that does not absorb said light, an active layer made of a semiconducting material absorbing incident light and a network of polarization electrodes collecting the detected signal, the electrodes network being arranged on the active layer, the electrodes network being composed of parallel conducting strips at a uniform spacing at a period less than the wavelength of incident light, the electrodes network forming a second mirror for the resonant cavity, wherein the light to be detected is incident to the device through the electrodes network, the optical characteristics of this second mirror being determined by the geometric dimensions of said conducting strips, the distance separating the first mirror from the second mirror being determined to obtain a Fabry-Pérot type resonance for incident light between these two mirrors.

**Claim 2 (Original):** Photo-detection device according to claim 1, wherein the reflecting means forming a first mirror are composed of a Bragg mirror.

**Claim 3 (Currently amended):** Photo-detection device according to claim 2, wherein the Bragg mirror is composed of alternating layers of AlAs and AlGaAs ~~and AlAs~~ and alternating layers of GaInAsP and InP or alternating layers of AlGaInAs and AlInAs or alternating layers of AlGaAsSb and AlAsSb.

**Claim 4 (Original):** Photo-detection device according to claim 1, wherein the reflecting means forming a first mirror are composed of a metallic layer.

**Claim 5 (Original):** Photo-detection device according to claim 4, wherein the metallic layer forming the first mirror provides a silver, gold or aluminium surface to incident light.

**Claim 6 (Original):** Photo-detection device according to claim 1, wherein the reflecting means forming a first mirror are composed of a multilayer dielectric mirror.

**Claim 7 (Original):** Photo-detection device according to claim 1, wherein the layer of material that does not absorb light is made of  $\text{Al}_x\text{Ga}_{1-x}\text{As}$  and the active layer is made of GaAs.

**Claim 8 (Original):** Photo-detection device according to claim 7, wherein x is of the order of 0.35.

**Claim 9 (Original):** Photo-detection device according to claim 1, wherein the layer of material that does not absorb light is made of AlInAs and the active layer is made of InGaAs.

**Claim 10 (Original):** Photo-detection device according to claim 1, wherein the electrodes network forms two interdigitated combs.

**Claim 11 (Canceled)**

**Claim 12 (Original):** Photo-detection device according to claim 1, wherein the conducting strips are made of silver or gold or aluminium.

**Claim 13 (Original):** Photo-detection device according to claim 1, wherein a passive layer of dielectric material is deposited on the electrodes network.

**Claim 14 (Original):** Photo-detection device according to claim 13, wherein the passivation layer is made of silicon dioxide or silicon nitride.

**Claim 15 (Original):** Photo-detection device according to claim 1, wherein a second face of the support supports an electrode to apply an electrical field to the device to change the resonant wavelength of the resonant cavity by the opto-electric effect.